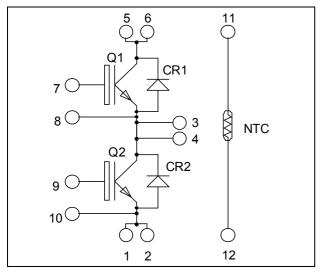
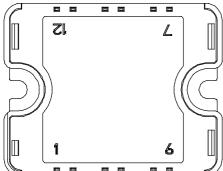


### Phase leg Trench + Field Stop IGBT3 Power Module





Pins 1/2; 3/4; 5/6 must be shorted together

# $V_{CES} = 600V$ $I_C = 75A$ @ Tc = 80°C

#### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### **Features**

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
  - Very low stray inductance
    - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

#### **Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

#### **Absolute maximum ratings**

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		600	V
Ţ	Continuous Collector Current	$T_C = 25^{\circ}C$	100	
$I_{\rm C}$	Continuous Conector Current	$T_C = 80$ °C	75	Α
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	140	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Maximum Power Dissipation	$T_C = 25^{\circ}C$	250	W
RBSOA	Reverse Bias Safe Operating Area	$T_{J} = 150^{\circ}C$	150A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



# All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μA
V <sub>CE(sat)</sub>	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.5	1.9	V
V CE(sat)		$I_C = 75A$ $T_j = 150^{\circ}C$		1.7		·	
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 600 \mu A$		5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				600	nA

### **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			4620		
Coes	Output Capacitance				300		pF
$C_{res}$	Reverse Transfer Capacitance				140		ĺ
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)			110		
T <sub>r</sub>	Rise Time	$V_{GE} = \pm 15V$			45		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 300V$ $I_{C} = 75A$			200		
$T_{\mathrm{f}}$	Fall Time	$R_G = 4.7\Omega$			40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch $V_{GE} = \pm 15V$	ing (150°C)		120		
$T_{r}$	Rise Time	$V_{\text{Bus}} = 300 \text{V}$			50		ns
$T_{d(off)}$	Turn-off Delay Time	$I_C = 75A$			250		
$T_{\rm f}$	Fall Time	$R_G = 4.7\Omega$			60		
Eon	$V_{GE} = \pm 15V$	$V_{GE} = \pm 15V$	$T_j = 25^{\circ}C$		0.35		mJ
Lon	Turn-on Switching Energy	$V_{\text{Bus}} = 300V$	$T_{j} = 150^{\circ}C$	•	0.6		1113
E <sub>off</sub>	Turn-off Switching Energy $I_C = 75A$ $R_G = 4.7\Omega$		$T_j = 25^{\circ}C$		2.2		mJ
Loff		$T_{j} = 150^{\circ}C$		2.6		1117	

### Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			600			V
$I_{RM}$	Maximum Reverse Leakage Current	V <sub>R</sub> =600V	$T_j = 25^{\circ}C$ $T_i = 150^{\circ}C$			250 500	μΑ
$I_{\mathrm{F}}$	DC Forward current		$T_j = 130 \text{ C}$ $Tc = 80^{\circ}\text{C}$		75	300	A
$V_{\rm F}$	Diode Forward Voltage	$I_F = 75A$ $V_{GE} = 0V$	$T_i = 25$ °C $T_i = 150$ °C		1.6 1.5	2	V
t <sub>rr</sub>	Reverse Recovery Time		$T_j = 25^{\circ}C$ $T_i = 150^{\circ}C$		100 150		ns
Q <sub>rr</sub>	Reverse Recovery Charge	$\begin{split} I_F = 75A \\ V_R = 300V \\ di/dt = 2000A/\mu s \end{split}$	$T_j = 150 \text{ C}$ $T_j = 25^{\circ}\text{C}$		3.6		μС
✓rr	reverse receivery charge		$T_j = 150^{\circ}C$		7.6		μΟ
$E_{r}$	Reverse Recovery Energy		$T_{j} = 25^{\circ}C$ $T_{j} = 150^{\circ}C$		0.85		mJ



### Thermal and package characteristics

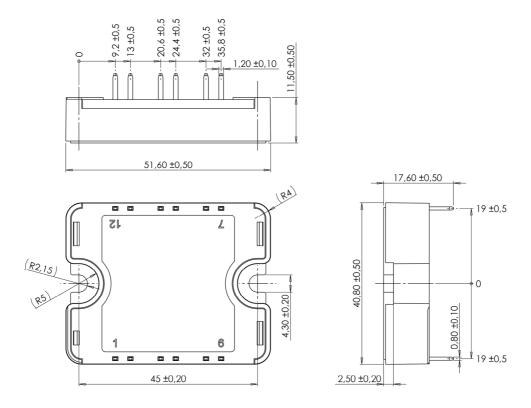
Symbol	Characteristic			Min	Тур	Max	Unit
$R_{\text{thJC}}$	Junction to Case Thermal Resistance		IGBT			0.60	°C/W
	Junction to Case Thermal Resistance		Diode			0.98	C/ W
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range			-40		175	
$T_{STG}$	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature					100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight				80	g	

### Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B <sub>25/85</sub>	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]} \quad \text{T: Thermistor temperature } \\ R_{T}: \text{ Thermistor value at T}$$

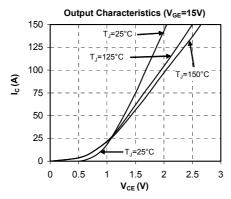
### SP1 Package outline (dimensions in mm)

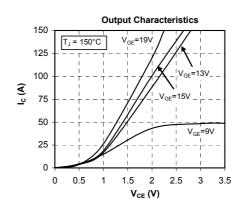


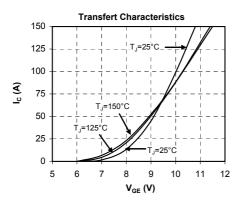
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

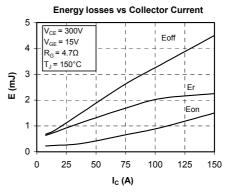


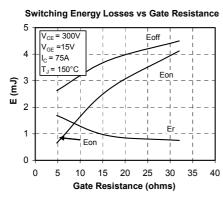
### **Typical Performance Curve**

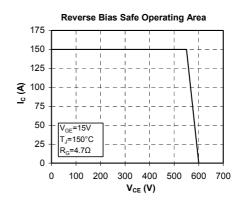


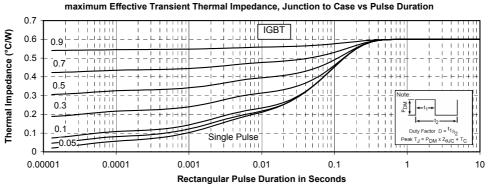




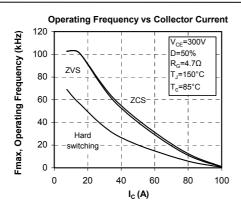


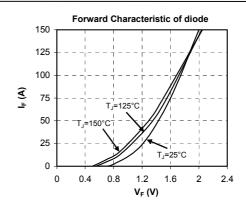


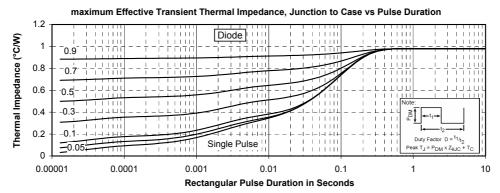














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